



2822

#7C

PATENT  
Customer No. 222,852  
Attorney Docket No. 04329.1949-01

71-03

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: )  
)  
Atsushi YAGISHITA, et al. ) Group Art Unit: 2822  
)  
Application No.: 10/023,849 ) Examiner: Rose, Kiesha L.  
)  
Filed: December 21, 2001 )  
)  
For: SEMICONDUCTOR DEVICE (AS )  
AMENDED) )

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

RECEIVED  
JUN - 3 2003  
TECHNOLOGY CENTER 2800

AMENDMENT

In reply to the Office Action of March 31, 2003, with a period for response extending through June 30, 2003, please amend the application as follows. Applicants also respectfully request the Examiner's reconsideration in view of the following remarks:

IN THE DRAWINGS:

Submitted herewith is a Request for Approval of Drawing Changes in which proposed changes to Fig. 16X are indicated in red ink.

IN THE ABSTRACT:

Please replace the current Abstract with the Substitute Abstract attached on a separate page. The full text of the Abstract in clean form is as follows:

--There is provided a semiconductor device including a substrate, a device isolation insulating film formed on the substrate, a gate electrode formed on the substrate, a gate wiring

FINNEGAN  
HENDERSON  
FARABOW  
GARRETT &  
DUNNER LLP

1300 I Street, NW  
Washington, DC 20005  
202.408.4000  
Fax 202.408.4400  
www.finnegan.com